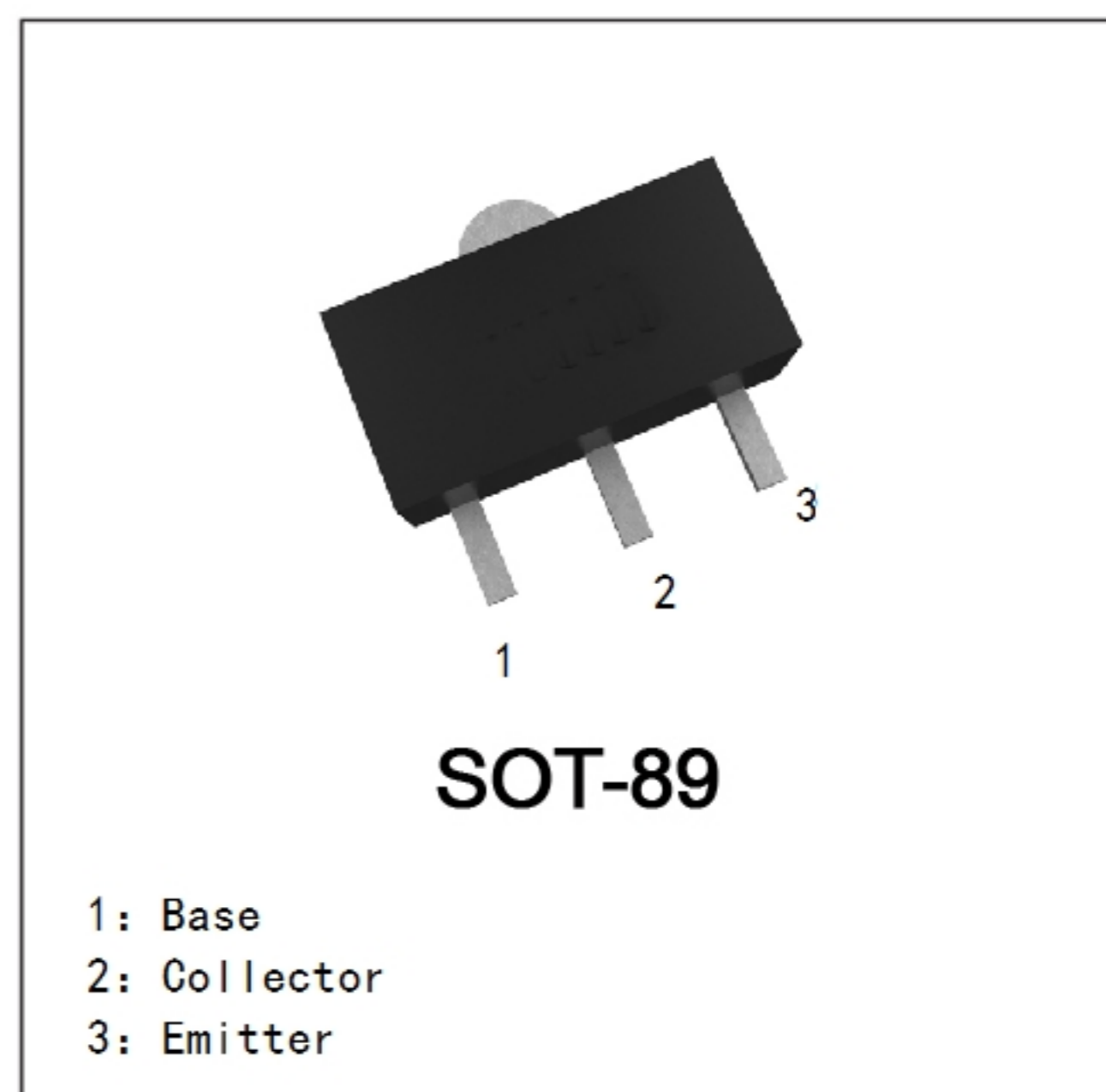


## ● Features

- World standard miniature package:SOT-89
- High collector to base voltage: $V_{CB0} > -100V$
- Excellent DC current gain linearity.



## ● Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector to base voltage	$V_{CB0}$	-100	V
Collector to emitter voltage	$V_{CEO}$	-80	V
Emitter to base voltage	$V_{EBO}$	-5	V
Collector current	$I_C$	-1	A
Collector current(Pulse) *	$I_C$	-1.5	A
Total power dissipation	$P_T$	2	W
Junction temperature	$T_j$	150	$^\circ C$
Storage temperature range	$T_{stg}$	-55 to +150	$^\circ C$

\*  $PW \leq 10ms, duty\ cycle \leq 50\%$ .

## ● Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	$I_{CBO}$	$V_{CB} = -100 V, I_E = 0$			-100	nA
Emitter cutoff current	$I_{EBO}$	$V_{EB} = -5.0 V, I_C = 0$			-100	nA
DC current gain *	$h_{FE}$	$V_{CE} = -2.0 V, I_C = -100 mA$	90	200	400	
		$V_{CE} = -2.0 V, I_C = -500 mA$	25	80		
Collector saturation voltage *	$V_{CE(sat)}$	$I_C = -500mA, I_B = -50mA$		-0.29	-0.5	V
Base saturation voltage *	$V_{BE(sat)}$	$I_C = -500mA, I_B = -50mA$		-0.9	-1.5	V
Base-emitter voltage *	$V_{BE}$	$V_{CE} = -10 V, I_C = -10 mA$	-600	-640	-700	mV
Gain bandwidth product	$f_T$	$V_{CE} = -5.0 V, I_E = 10 mA$		80		MHz
Output capacitance	$C_{ob}$	$V_{CB} = -10 V, I_E = 0, f = 1.0 MHz$		26		pF

\* Pulsed:  $PW \leq 350 \mu s, duty\ cycle \leq 2\%$

## ● $h_{FE}$ Classification

Marking	AW	AV	AU
$h_{FE}$	90~180	135~270	200~400